# NPN/PNP Dual General Purpose Transistor

This transistor is designed for general purpose amplifier applications. It is housed in the SOT-563 which is designed for low power surface mount applications.

## **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

## **MAXIMUM RATINGS - NPN**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	45	V
Collector - Base Voltage	V <sub>CBO</sub>	50	V
Emitter - Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current – Continuous	I <sub>C</sub>	100	mAdc

## **MAXIMUM RATINGS - PNP**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	-45	V
Collector - Base Voltage	V <sub>CBO</sub>	-50	V
Emitter - Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current – Continuous	I <sub>C</sub>	-100	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

## THERMAL CHARACTERISTICS

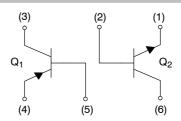
Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation (Note 1)  T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	357 2.9	mW mW/°C
Thermal Resistance – Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation (Note 1)  T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	500 4.0	mW mW/°C
Thermal Resistance – Junction-to-Ambient (Note 1)	$R_{\theta JA}$	250	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

<sup>1.</sup> FR-4 @ Minimum Pad



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BC847BPDX6T1



SOT-563 CASE 463A

## **MARKING DIAGRAM**



4F = Specific Device Code

M = Month Code■ = Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BC847BPDXV6T1G	SOT-563 (Pb-Free)	4 mm pitch 4000/Tape & Reel
SBC847BPDXV6T1G	SOT-563 (Pb-Free)	2 mm pitch 4000/Tape & Reel
BC847BPDXV6T5G	SOT-563 (Pb-Free)	2 mm pitch 8000/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS (NPN)** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	<b>-</b>				I.
Collector – Emitter Breakdown Voltage ( $I_C = 10 \text{ mA}$ )	V <sub>(BR)CEO</sub>	45	-	-	V
Collector – Emitter Breakdown Voltage ( $I_C = 10 \mu A, V_{EB} = 0$ )	V <sub>(BR)CES</sub>	50	-	-	V
Collector – Base Breakdown Voltage ( $I_C = 10 \mu A$ )	V <sub>(BR)CBO</sub>	50	-	-	V
Emitter – Base Breakdown Voltage ( $I_E = 1.0 \mu A$ )	V <sub>(BR)EBO</sub>	6.0	-	-	V
Collector Cutoff Current ( $V_{CB}$ = 30 V) ( $V_{CB}$ = 30 V, $T_{A}$ = 150°C)	I <sub>CBO</sub>	- -	- -	15 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain $ (I_C = 10 \ \mu\text{A}, \ V_{CE} = 5.0 \ \text{V}) $ $ (I_C = 2.0 \ \text{mA}, \ V_{CE} = 5.0 \ \text{V}) $	h <sub>FE</sub>	- 200	150 290	- 475	-
Collector – Emitter Saturation Voltage ( $I_C$ = 10 mA, $I_B$ = 0.5 mA) ( $I_C$ = 100 mA, $I_B$ = 5.0 mA)	V <sub>CE(sat)</sub>	-	- -	0.25 0.6	V
Base – Emitter Saturation Voltage ( $I_C$ = 10 mA, $I_B$ = 0.5 mA) ( $I_C$ = 100 mA, $I_B$ = 5.0 mA)	V <sub>BE(sat)</sub>	- -	0.7 0.9	- -	V
Base – Emitter Voltage ( $I_C$ = 2.0 mA, $V_{CE}$ = 5.0 V) ( $I_C$ = 10 mA, $V_{CE}$ = 5.0 V)	V <sub>BE(on)</sub>	580 -	660 -	700 770	mV
SMALL-SIGNAL CHARACTERISTICS					•
Current – Gain – Bandwidth Product ( $I_C$ = 10 mA, $V_{CE}$ = 5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	100	-	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 V, f = 1.0 MHz)	C <sub>obo</sub>	-	-	4.5	pF
Noise Figure (I <sub>C</sub> = 0.2 mA, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 2.0 k $\Omega$ , f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB

## ELECTRICAL CHARACTERISTICS (PNP) (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = -10 mA)	V <sub>(BR)CEO</sub>	-45	_	_	V
Collector – Emitter Breakdown Voltage ( $I_C = -10 \mu A$ , $V_{EB} = 0$ )	V <sub>(BR)CES</sub>	-50	_	-	V
Collector – Base Breakdown Voltage ( $I_C = -10 \mu A$ )	V <sub>(BR)CBO</sub>	-50	-	-	V
Emitter – Base Breakdown Voltage $(I_E = -1.0 \mu A)$	V <sub>(BR)EBO</sub>	-5.0	-	-	V
Collector Cutoff Current ( $V_{CB} = -30 \text{ V}$ ) ( $V_{CB} = -30 \text{ V}$ , $T_A = 150^{\circ}\text{C}$ )	Ісво	- -	_ _	-15 -4.0	nA μA
ON CHARACTERISTICS	<u> </u>				
DC Current Gain $ \begin{pmatrix} I_C = -10 \ \mu\text{A}, \ V_{CE} = -5.0 \ \text{V} \end{pmatrix} $ $ \begin{pmatrix} I_C = -2.0 \ \text{mA}, \ V_{CE} = -5.0 \ \text{V} \end{pmatrix} $	h <sub>FE</sub>	_ 200	150 290	- 475	-
Collector – Emitter Saturation Voltage ( $I_C = -10$ mA, $I_B = -0.5$ mA) ( $I_C = -100$ mA, $I_B = -5.0$ mA)	V <sub>CE(sat)</sub>	_ _	_ _	-0.3 -0.65	V
Base – Emitter Saturation Voltage ( $I_C = -10$ mA, $I_B = -0.5$ mA) ( $I_C = -100$ mA, $I_B = -5.0$ mA)	V <sub>BE(sat)</sub>	_ _	-0.7 -0.9	- -	V
Base – Emitter On Voltage ( $I_C = -2.0$ mA, $V_{CE} = -5.0$ V) ( $I_C = -10$ mA, $V_{CE} = -5.0$ V)	V <sub>BE(on)</sub>	-0.6 -	_ _	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product ( $I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz}$ )	f <sub>T</sub>	100	_	-	MHz
Output Capacitance (V <sub>CB</sub> = -10 V, f = 1.0 MHz)	C <sub>ob</sub>	-	_	4.5	pF
Noise Figure (I <sub>C</sub> = $-0.2$ mA, V <sub>CE</sub> = $-5.0$ Vdc, R <sub>S</sub> = $2.0$ k $\Omega$ , f = $1.0$ kHz, BW = $200$ Hz)	NF	-	_	10	dB

## TYPICAL NPN CHARACTERISTICS

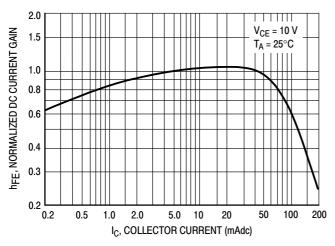


Figure 1. Normalized DC Current Gain

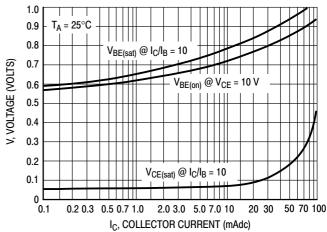


Figure 2. "Saturation" and "On" Voltages

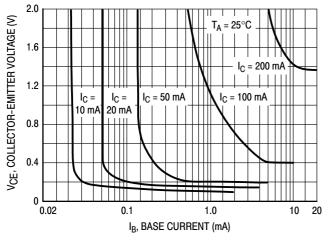


Figure 3. Collector Saturation Region

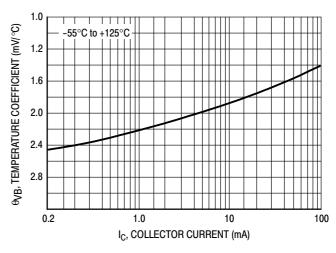


Figure 4. Base-Emitter Temperature Coefficient

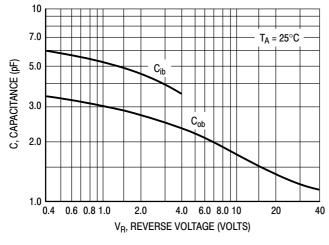


Figure 5. Capacitances

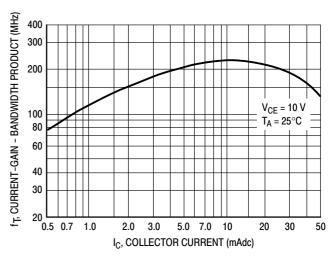
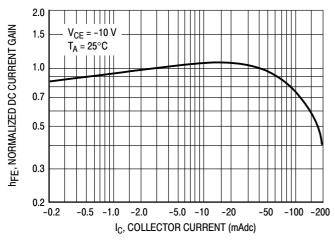


Figure 6. Current-Gain - Bandwidth Product

## TYPICAL PNP CHARACTERISTICS

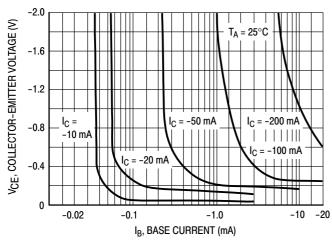
-1.0



-0.9 T<sub>A</sub> = 25°C  $V_{BE(sat)} @ I_C/I_B = 10$ -0.8 V, VOLTAGE (VOLTS) -0.7 V<sub>BE(on)</sub> @ V<sub>CE</sub> = -10 V -0.6 -0.5 -0.4 -0.3 -0.2  $V_{CE(sat)} @ I_C/I_B = 10$ -0.1 -0.2 -0.1 -5.0 -50 -100 IC, COLLECTOR CURRENT (mAdc)

Figure 7. Normalized DC Current Gain

Figure 8. "Saturation" and "On" Voltages



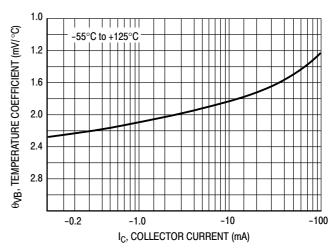
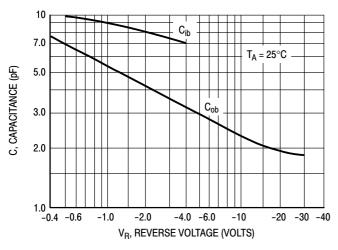


Figure 9. Collector Saturation Region

Figure 10. Base–Emitter Temperature Coefficient



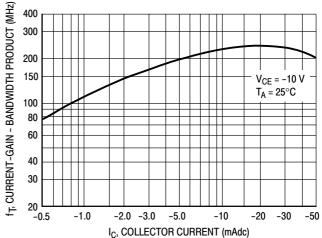
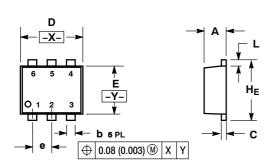


Figure 11. Capacitances

Figure 12. Current-Gain - Bandwidth Product

## PACKAGE DIMENSIONS

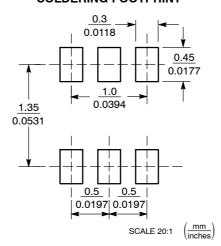
## SOT-563, 6 LEAD CASE 463A ISSUE F



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETERS
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MIL	LIMETE	RS	INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
е	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

## **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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